# International TOR Rectifier

### IR2184(4)(S)

#### HALF-BRIDGE DRIVER

#### **Features**

- Floating channel designed for bootstrap operation Fully operational to +600V Tolerant to negative transient voltage dV/dt immune
- Gate drive supply range from 10 to 20V
- Undervoltage lockout for both channels
- 3.3V and 5V input logic compatible
- Matched propagation delay for both channels
- Logic and power ground +/- 5V offset.
- Lower di/dt gate driver for better noise immunity
- Output source/sink current capability 1.4A/1.8A

# 8-Lead SOIC IR2184S 8-Lead PDIP IR21844 8-Lead PDIP IR21844

#### **Description**

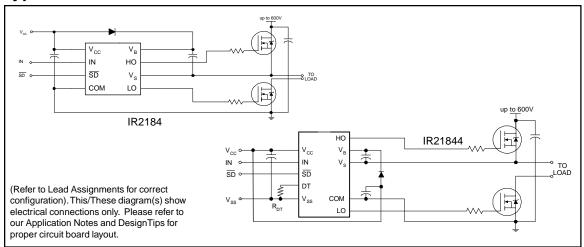
The IR2184(4)(S) are high voltage, high speed power MOSFET and IGBT drivers with dependent high and low side referenced output channels. Proprietary HVIC and latch immune CMOS technologies enable rugge-dized monolithic construction. The logic input is compatible with standard CMOS or LSTTL output, down to 3.3V logic. The output drivers feature a high pulse current buffer stage designed for

#### IR2181/IR2183/IR2184 Feature Comparison

Part	Input logic	Cross- conduction prevention logic	Dead-Time	Ground Pins	Ton/Toff	
2181	HIN/LIN	no	none	COM	180/220 ns	
21814	TIIIN/LIIN	110	none	VSS/COM	100/220118	
2183	HIN/LIN	ves	Internal 500ns	COM	180/220 ns	
21834	TIIIN/LIIN	yes	Program 0.4 ~ 5 us	VSS/COM	100/220115	
2184	IN/SD	yes	Internal 500ns	COM	680/270 ns	
21844	IIV/SD	yes	Program 0.4 ~ 5 us	VSS/COM	000/270113	

minimum driver cross-conduction. The floating channel can be used to drive an N-channel power MOSFET or IGBT in the high side configuration which operates up to 600 volts.

#### **Typical Connection**



#### **Absolute Maximum Ratings**

Absolute maximum ratings indicate sustained limits beyond which damage to the device may occur. All voltage parameters are absolute voltages referenced to COM. The thermal resistance and power dissipation ratings are measured under board mounted and still air conditions.

Symbol	Definition	Min.	Max.	Units	
V <sub>B</sub>	High side floating absolute voltage	-0.3	625		
Vs	High side floating supply offset voltage	V <sub>B</sub> - 25	V <sub>B</sub> + 0.3		
VHO	High side floating output voltage		Vs - 0.3	V <sub>B</sub> + 0.3	
V <sub>CC</sub>	Low side and logic fixed supply voltage		-0.3	25	1
$V_{LO}$	Low side output voltage		-0.3	V <sub>CC</sub> + 0.3	V
DT	Programmable dead-time pin voltage (IR21	844 only)	V <sub>SS</sub> - 0.3	V <sub>CC</sub> + 0.3	
VIN	Logic input voltage (IN & SD)		V <sub>SS</sub> - 0.3	V <sub>SS</sub> + 10	
V <sub>SS</sub>	Logic ground (IR21844 only)		V <sub>CC</sub> - 25	V <sub>CC</sub> + 0.3	
dV <sub>S</sub> /dt	Allowable offset supply voltage transient		_	50	V/ns
P <sub>D</sub>	Package power dissipation @ T <sub>A</sub> ≤ +25°C	(8-lead PDIP)	_	1.0	
		(8-lead SOIC)	_	0.625	
		(14-lead PDIP)	_	1.6	W
		(14-lead SOIC)	_	1.0	
Rth <sub>JA</sub>	Thermal resistance, junction to ambient	(8-lead PDIP)	_	125	
		(8-lead SOIC)	_	200	l
		(14-lead PDIP)	_	75	°C/W
		(14-lead SOIC)	_	120	Ī
TJ	Junction temperature		_	150	
T <sub>S</sub>	Storage temperature		-50	150	°C
TL	Lead temperature (soldering, 10 seconds)		_	300	

#### **Recommended Operating Conditions**

The input/output logic timing diagram is shown in figure 1. For proper operation the device should be used within the recommended conditions. The Vs and Vss offset rating are tested with all supplies biased at 15V differential.

Symbol	Definition	Min.	Max.	Units
VB	High side floating supply absolute voltage	V <sub>S</sub> + 10	V <sub>S</sub> + 20	
Vs	High side floating supply offset voltage	Note 1	600	
V <sub>HO</sub>	High side floating output voltage	Vs	V <sub>B</sub>	
V <sub>CC</sub>	Low side and logic fixed supply voltage	10	20	
V <sub>LO</sub>	Low side output voltage	0	Vcc	V
V <sub>IN</sub>	Logic input voltage (IN & SD)	V <sub>SS</sub>	V <sub>SS</sub> + 5	
DT	Programmable dead-time pin voltage (IR21844 only)	V <sub>SS</sub>	Vcc	
V <sub>SS</sub>	Logic ground (IR21844 only)	-5	5	
T <sub>A</sub>	Ambient temperature	-40	125	°C

Note 1: Logic operational for Vs of -5 to +600V. Logic state held for Vs of -5V to -VBs. (Please refer to the Design Tip DT97-3 for more details).

Note 2: IN and SD are internally clamped with a 5.2V zener diode.

#### **Dynamic Electrical Characteristics**

 $V_{BIAS}$  (V<sub>CC</sub>, V<sub>BS</sub>) = 15V, V<sub>SS</sub> = COM, C<sub>L</sub> = 1000 pF, T<sub>A</sub> = 25°C, DT = VSS unless otherwise specified.

Symbol	Definition		Тур.	Max.	Units	<b>Test Conditions</b>
ton	Turn-on propagation delay	_	680	900		Vs = 0V
toff	Turn-off propagation delay	_	270	400		V <sub>S</sub> = 0V or 600V
tsd	Shut-down propagation delay	_	180	270		
MTon	Delay matching, HS & LS turn-on	_	0	90	nsec	
MToff	Delay matching, HS & LS turn-off		0	40		
t <sub>r</sub>	Turn-on rise time	_	40	60		V <sub>S</sub> = 0V
tf	Turn-off fall time	_	20	35		V <sub>S</sub> = 0V
DT	Deadtime: LO turn-off to HO turn-on(DTLO-HO) &	280	400	520		RDT= 0
	HO turn-off to LO turn-on (DTHO-LO)	4	5	6	μsec	RDT = 200k
MDT	Deadtime matching = DTLO - HO - DTHO-LO	_	0	50	ncoc	RDT=0
		_	0	600	nsec	RDT = 200k

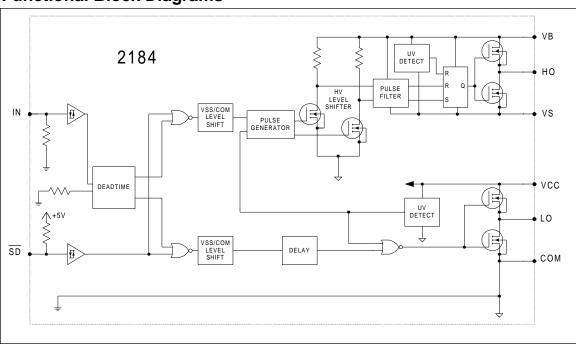
#### **Static Electrical Characteristics**

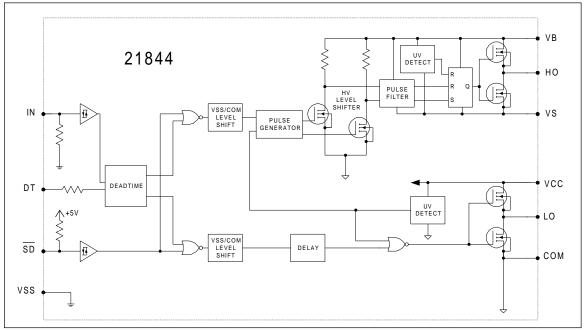
 $V_{BIAS}$  (V<sub>CC</sub>, V<sub>BS</sub>) = 15V, V<sub>SS</sub> = COM, DT= V<sub>SS</sub> and T<sub>A</sub> = 25°C unless otherwise specified. The  $V_{IL}$ , V<sub>IH</sub> and I<sub>IN</sub> parameters are referenced to V<sub>SS</sub> /COM and are applicable to the respective input leads: IN and  $\overline{SD}$ . The V<sub>O</sub>, I<sub>O</sub> and Ron parameters are referenced to COM and are applicable to the respective output leads: HO and LO.

Symbol	Definition		Тур.	Max.	Units	<b>Test Conditions</b>
VIH	Logic "1" input voltage for HO & logic "0" for LO	2.7	_	_		V <sub>CC</sub> = 10V to 20V
V <sub>IL</sub>	Logic "0" input voltage for HO & logic "1" for LO		_	0.8		V <sub>CC</sub> = 10V to 20V
V <sub>SD,TH+</sub>	SD input positive going threshold	2.7	_	_	V	V <sub>CC</sub> = 10V to 20V
V <sub>SD,TH</sub> -	SD input negative going threshold	_	_	0.8		V <sub>CC</sub> = 10V to 20V
Voн	High level output voltage, V <sub>BIAS</sub> - V <sub>O</sub>	_	_	1.2		I <sub>O</sub> = 0A
V <sub>OL</sub>	Low level output voltage, VO	_	_	0.1		I <sub>O</sub> = 0A
I <sub>LK</sub>	Offset supply leakage current	_	_	50		$V_{B} = V_{S} = 600V$
I <sub>QBS</sub>	Quiescent V <sub>BS</sub> supply current	20	60	150	μA	V <sub>IN</sub> = 0V or 5V
IQCC	Quiescent V <sub>CC</sub> supply current	0.4	1.0	1.6	mA	V <sub>IN</sub> = 0V or 5V
I <sub>IN+</sub>	Logic "1" input bias current		5	20	μA	$IN = 5V, \overline{SD} = 0V$
I <sub>IN-</sub>	Logic "0" input bias current	_	1	2	μΑ	$IN = 0V, \overline{SD} = 5V$
V <sub>CCUV+</sub> V <sub>BSUV+</sub>	$V_{CC}$ and $V_{BS}$ supply undervoltage positive going threshold	8.0	8.9	9.8		
V <sub>CCUV</sub> - V <sub>BSUV</sub> -	V <sub>CC</sub> and V <sub>BS</sub> dupply undervoltage negative going threshold	7.4	8.2	9.0	,,	
Vссиvн	Hysteresis		0.7	_	V	
V <sub>BSUVH</sub>						
I <sub>O+</sub>	Output high short circuit pulsed vurrent	1.4	1.9	_		$V_O = 0V$ ,
		1.8				PW ≤ 10 µs
I <sub>O-</sub>	Output low short circuit pulsed current		2.3	-	] A	$V_{O} = 15V$ ,
						PW ≤ 10 µs

# IR2184(4) (S)

## **Functional Block Diagrams**

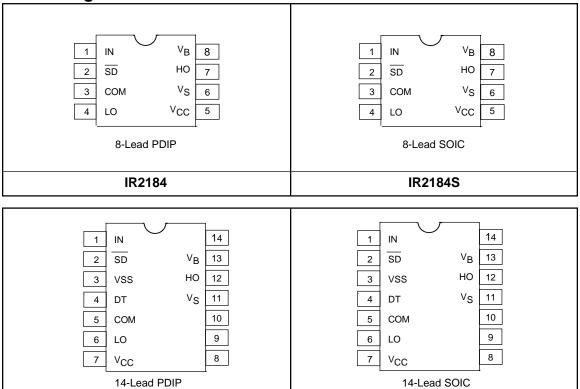




#### **Lead Definitions**

Symbol	Description
IN	Logic input for high and low side gate driver outputs (HO and LO), in phase with HO (referenced to COM
	for IR2184 and VSS for IR21844)
SD	Logic input for shutdown (referenced to COM for IR2184 and VSS for IR21844)
DT	Programmable dead-time lead, referenced to VSS. (IR21844 only)
VSS	Logic Ground (21844 only)
V <sub>B</sub>	High side floating supply
НО	High side gate drive output
Vs	High side floating supply return
Vcc	Low side and logic fixed supply
LO	Low side gate drive output
СОМ	Low side return

**Lead Assignments** 

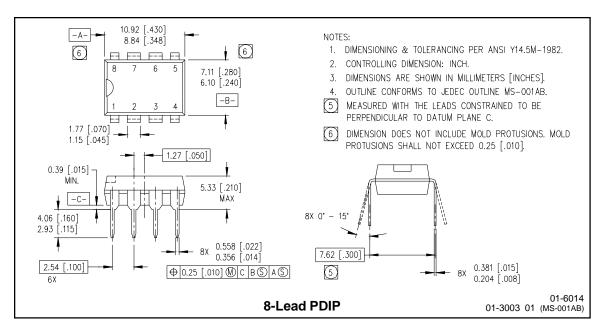


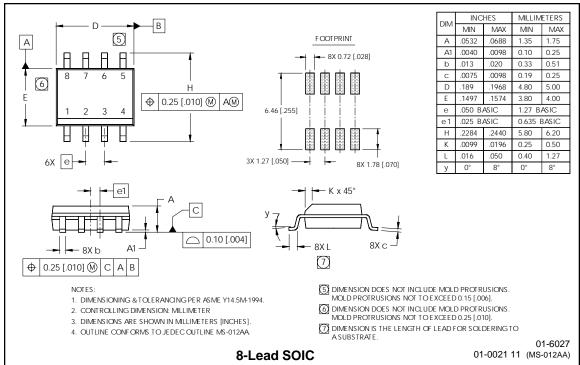
www.irf.com 5

IR21844S

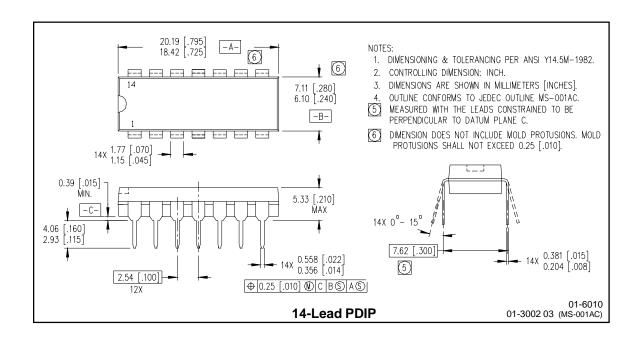
IR21844

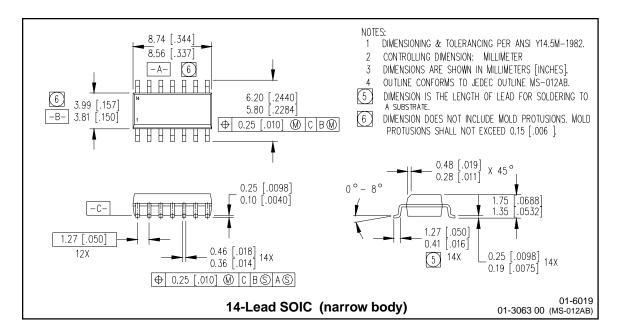
# IR2184(4) (S)





# IR2184(4) (S)





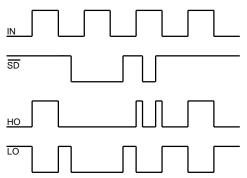


Figure 1. Input/Output Timing Diagram

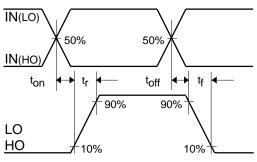


Figure 2. Switching Time Waveform Definitions

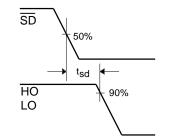


Figure 3. Shutdown Waveform Definitions

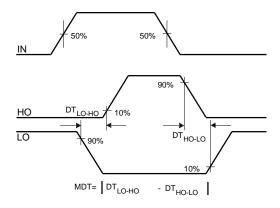


Figure 4. Deadtime Waveform Definitions

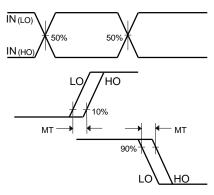


Figure 5. Delay Matching Waveform Definitions

International

IR Rectifier

IR WORLD HEADQUARTERS: 233 Kansas St., El Segundo, California 90245 Tel: (310) 252-7105

Data and specifications subject to change without notice. 7/24/2001